

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

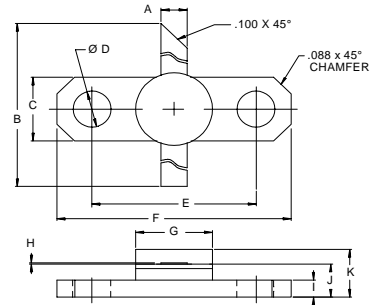
The **ASI AVD090F** is Designed for High Peak power & low duty cycle, IFF, DME, and TACAN Applications.

**FEATURES:**

- Internal Input Matching Network
- $P_G = 8.4$  dB at 90 W/1150 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	1.0 A PEAK
$V_{CB}$	55 V
$P_{DISS}$	292 W @ 25 °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	0.6 °C/W

**PACKAGE STYLE .250 2L FLG (B)**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	1.050 / 26.67	
C	.245 / 6.22	.255 / 6.48
D	.120 / 3.05	.140 / 3.56
E	.552 / 14.02	.572 / 14.53
F	.790 / 20.07	.810 / 20.57
G		.285 / 7.24
H	.003 / 0.08	.007 / 0.18
I	.052 / 1.32	.072 / 1.83
J	.120 / 3.05	.130 / 3.30
K		.210 / 5.33

**ORDER CODE: ASI10562**
**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 10$ mA	65			V
$BV_{CER}$	$I_C = 25$ mA $R_{BE} = 10$ $\Omega$	65			V
$BV_{EBO}$	$I_E = 1.0$ mA	3.5			V
$I_{CES}$	$V_{CB} = 50$ V			100	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		200	---
$C_{OB}$	$V_{CE} = 50$ V $f = 1.0$ MHz			40	pF
$P_G$	$V_{CC} = 50$ V $P_{OUT} = 90$ W $f = 1025 - 1150$ MHz	8.4			dB
$\eta_c$	$P_{IN} = 13$ W		38		%

Pulse with = 10  $\mu$ S, Duty Cycle = 1.0 %

**IMPEDANCE DATA** **$P_{IN} = 13 \text{ w}$**  **$V_{CE} = 50 \text{ V}$** 

FREQ	$Z_{IN} (\Omega)$	$Z_{CL} (\Omega)$
960 MHz	$2.5 + j13.0$	$4.6 - j5.5$
1030 MHz	$5.2 + j15.0$	$5.0 - j5.5$
1090 MHz	$16.3 + j15.0$	$4.8 - j5.5$
1150 MHz	$14.7 + j2.5$	$4.7 - j7.0$
1215 MHz	$7.6 + j0.5$	$4.7 - j5.0$